

<<固态电子器件>>

图书基本信息

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内容概要

本书是介绍半导体器件工作原理的经典入门教材，其主要内容包括固体物理基础和半导体器件物理两大部分，同时也涵盖半导体晶体结构与材料生长技术、集成电路原理与制造工艺以及光电子器件与高频大功率器件等相关内容。

本书注重基本物理概念，强调理论联系实际，可作为高等院校电子信息类专业“固态器件与电路”专业基础课的教材，也可供相关领域的研究人员和技术人员参考。

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Streetman教授的教

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